



PATENT APPLICATION

#18/5
5-22-2
Snyder

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Tomoyoshi KUSHIDA

Application No.: 09/435,766

Filed: November 8, 1999

For: SEMICONDUCTOR DEVICE

Group Art Unit: 2811

Examiner: S. Loke

Docket No.: 104361

RECEIVED
MAY 21 2002
TC 2800 MAIL ROOM

PRELIMINARY AMENDMENT

Director of the U.S. Patent and Trademark Office
Washington, D. C. 20231

Sir:

Prior to initial examination, please amend the above-identified application as follows:

IN THE CLAIMS:

Please replace claims 1 and 4 as follows:

1. (Four Times Amended) A bipolar semiconductor device comprising:

E! Subj
a drain electrode;

*figs. 1A, 1B,
5,*
a drain region having a first conductive type semiconductor and disposed on
the drain electrode;

*f. 7,
lines 3-8*
a drift region having a second conductive type semiconductor different from
the first conductive type semiconductor of the drain region and disposed on the drain region;

a channel region having the second conductive type semiconductor and
disposed on the drift region;

*a gate region surrounding at least a part of the channel region via an insulation
film, the gate region having the first conductive type semiconductor;*